

Title (en)

OPTOELECTRONIC SEMICONDUCTOR CHIP AND METHOD FOR PRODUCING AN OPTOELECTRONIC SEMICONDUCTOR CHIP

Title (de)

OPTOELEKTRONISCHER HALBLEITERCHIP UND VERFAHREN ZUR HERSTELLUNG EINES OPTOELEKTRONISCHEN HALBLEITERCHIPS

Title (fr)

PUCE SEMI-CONDUCTRICE OPTOÉLECTRONIQUE ET PROCÉDÉ DE FABRICATION D'UNE PUCE SEMI-CONDUCTRICE OPTOÉLECTRONIQUE

Publication

**EP 3853913 A1 20210728 (DE)**

Application

**EP 19769789 A 20190916**

Priority

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Abstract (en)

[origin: WO2020058180A1] In at least one embodiment, the optoelectronic semiconductor chip (100) comprises a semiconductor layer sequence (1) and several semiconductor structures (21, 22) having in each case one active region (210). The active regions are respectively designed for the emission and/or absorption of electromagnetic radiation. The active regions of different semiconductor structures are not linked to one another. The semiconductor structures are respectively designed as a nanorod or a microrod. The semiconductor structures are embedded in the semiconductor layer sequence.

IPC 8 full level

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CPC (source: EP US)

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Citation (search report)

See references of WO 2020058180A1

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